

isc Silicon NPN Power Transistor

2SD860

DESCRIPTION

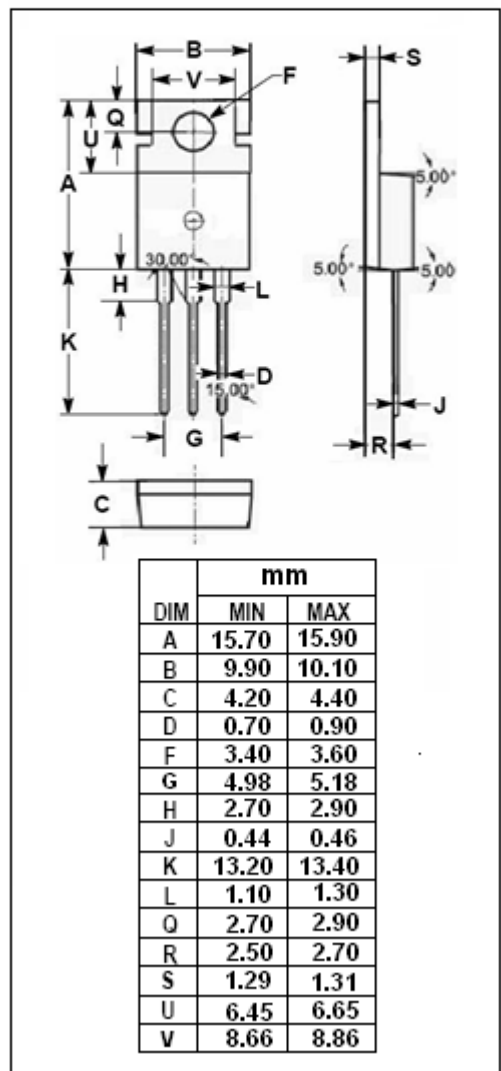
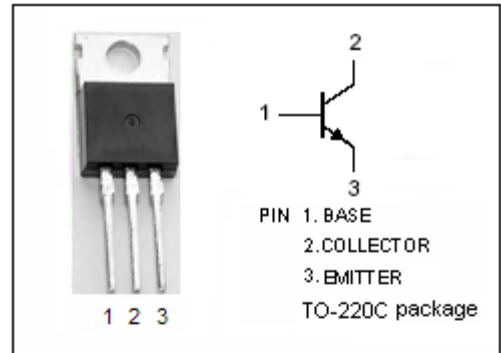
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 250V(\text{Min})$
- High Collector Power Dissipation

APPLICATIONS

- Designed for AF power amplifier applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	350	V
$V_{CEO}$	Collector-Emitter Voltage	250	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	1	A
$I_{CM}$	Collector Current-Peak	2	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SD860****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=30\text{mA}; I_B=0$	250			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.4\text{A}$			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=2\text{A}; V_{CE}=10\text{V}$			1.5	V
$I_{CEO}$	Collector Cutoff Current	$V_{CE}=150\text{V}; I_B=0$			1	mA
$I_{CES}$	Collector Cutoff Current	$V_{CE}=350\text{V}; V_{BE}=0$			1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1	mA
$h_{FE-1}$	DC Current Gain	$I_C=0.3\text{A}; V_{CE}=10\text{V}$	40		250	
$h_{FE-2}$	DC Current Gain	$I_C=2\text{A}; V_{CE}=10\text{V}$	10			

## Switching Times

$t_{on}$	Turn-On Time	$I_C=2\text{A}; I_{B1}=-I_{B2}=0.2\text{A}$		0.2		$\mu\text{s}$
$t_{off}$	Turn-Off Time			2.0		$\mu\text{s}$

◆  $h_{FE-1}$  Classifications

R	Q	P
40-90	70-150	120-250